

SEMICONDUCTOR SUBSTRATE AND METHOD OF PRODUCTION

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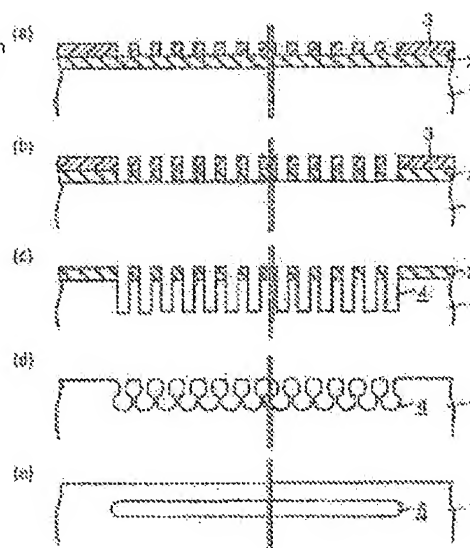
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Abstract of JP 2001144276 (A)

PROBLEM TO BE SOLVED: To form an SOI structure without causing cost increase or lowering of reliability. SOLUTION: A plurality of grooves 4 are made in the surface of a silicon substrate 1 while being arranged two-dimensionally and then the silicon substrate 1 is heat treated to deform the plurality of grooves 4 into one planar cavity 5.



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